ON Semiconductor

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #20392

Generic Copy

Issue Date: 03-Apr-2014

TITLE: Qualification of ONC18EE process technology for EEPROM Memory fabrication at ON Semiconductor's Gresham, Oregon.

PROPOSED FIRST SHIP DATE: 03-Jul-2014 or earlier upon customers' approval

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Fabrication Site

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:
Contact your local ON Semiconductor Sales Office or Julio Song<julio.song@onsemi.com>

SAMPLES:
Contact your local ON Semiconductor Sales Office

ADDITIONAL RELIABILITY DATA: Available
Contact your local ON Semiconductor Sales Office or Francis Lualhati <ffxczy@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

ON Semiconductor is pleased to announce that, as part of its ongoing effort to improve product availability, the I^2C EEPROM devices listed in this FPCN are now qualified for production in the 0.18 µm CMOS EE process at ON Semiconductor's 8-inch Wafer Fab in Gresham, Oregon, USA. The Gresham Wafer Fab is ISO9001:2008, ISO/TS16949:2009 and ISO14001:2004 certified.

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RELIABILITY DATA SUMMARY:

Qual Vehicles: CAT24C64WI-GT3

Qualification Results and Analysis:

Test:	Conditions:	Interval:	Result
HTOL	TA=150°C, Biased	1008 hrs	0/240
ELFR	TA=150°C, Biased	24 hrs	0/2400
EDR(Endurance)	TA=25°C	1 Mil cycle	0/240
EDR(NVM Data Retention)	TA=150°C	1008 hrs	0/240
HTSL	TA=150°C	1008 hrs	0/240
HAST+PC	Ta=130C RH=85%	96 hrs	0/240
TC+PC	Ta= -65 C to +150 C	500 cyc	0/240
Autoclave+PC	Ta=121C RH=100% ~15 psig	96 hrs	0/240
DPA	Following HTSL		0/6
DPA	Following TC+PC		0/6

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DPA	Following TC+PC		0/6

Conclusion: All reliability requirements have been met.

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ELECTRICAL CHARACTERISTIC SUMMARY:

Device parameters will continue to meet all datasheet specifications. Characterization data is available upon request. Even though device specifications remain unchanged, ON Semiconductor recommends samples be obtained for application specific review.

CHANGED PART IDENTIFICATION:

Device marking will not change.

List of Affected General Parts:

CAT24C02HU4IGT3A	CAT24C08WI-GT3	CAT24C32WI-GT3
CAT24C02WI-G	CAT24C08WI-GT3JN	CAT24C32WI-GT3JN
CAT24C02WI-GT3	CAT24C08YE-GT3	CAT24C32YI-G
CAT24C02WI-GT3A	CAT24C08YI-G	CAT24C32YI-GT3
CAT24C02WI-GT3JN	CAT24C08YI-GT3	CAT24C32YI-GT3JN
CAT24C02YI-G	CAT24C164WI-G	CAT24C64HU4I-GT3
CAT24C02YI-GT3	CAT24C164WI-GT3	CAT24C64WI-G
CAT24C02YI-GT3A	CAT24C164YI-GT3	CAT24C64WI-GT3
CAT24C04HU4I-GT3	CAT24C16HU4I-GT3	CAT24C64WI-GT3JN
CAT24C04WI-G	CAT24C16WE-GT3	CAT24C64XI-T2
CAT24C04WI-GT3	CAT24C16WI-G	CAT24C64YI-G
CAT24C04WI-GT3JN	CAT24C16WI-GT3	CAT24C64YI-GT3
CAT24C04YI-G	CAT24C16WI-GT3JN	CAT24C64YI-GT3JN
CAT24C04YI-GT3	CAT24C16YI-G	CAT34C02HU4IGT4A
CAT24C04YI-GT3JN	CAT24C16YI-GT3	CAT34C02YI-G
CAT24C08HU4I-GT3	CAT24C32HU4I-GT3	CAT34C02YI-GT5
CAT24C08WI-G	CAT24C32WI-G	CAT34C02YI-GT5A